



Institute of High Energy Physics
Chinese Academy of Sciences

SuperEM: Next-Generation Sub-meV Threshold Cryogenic Neutrino Detectors

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IHEP

Guangzhou, 16/07/2026

本人研究背景介绍



- **HERD, 5面灵敏3D成像量能器方案共同提出人和原型完成人, 2029.03发射** Talk by X.L. Sun at CALOR 2010; Paper by X.L. Sun et al. 2011 J. Phys.: Conf. Ser. 293 012038; PhD thesis of X.L. Sun 2011.
- **Dark Matter, 暗物质探测双发光晶体方案提出人和原型完成人** Talk by X.L. Sun at IHEP-INFN Meeting 2014; Paper by X. Zhang, X.L. Sun, J.G. Lu et al. RDTM 2, 15 (2018).
- **GECAM, SiPM+LaBr₃ 空间伽马射线探测器方案提出人和原型完成人, 2020.12发射, 在轨运行** Talk by X.L. Sun at PISA Meeting 2018; Paper by P. Lv, S.L. Xiong, X.L. Sun et al. 2018 JINST 13 P08014.
- **CEvNS, 低温CsI+SiPM+TPB探测器方案提出人和原型完成人** Talk by X.L. Sun at CEvNS 2024; Paper by L. Wang, G.D. Li, X.L. Sun et al. Eur. Phys. J. C 84, 440 (2024).
- **JUNO, 2万吨超纯液闪混制任务负责人, 2025.08完成, 运行取数** Poster by X.L. Sun at Neutrino 2024; Paper by J.Y. Shao, W.J. Li, X.L. Sun et al. RDTM (2026), doi.org/10.1007/s41605-026-00708-y.
- **Gamma/Neutron, 重点研发课题超高能量分辨率及多模辐射探测器研制负责人, 2025.10完成**, 中国辐射防护学会科学技术奖-特等奖, 吴云涛, 孙希磊等2024-FM-T-02-R7; 国家标准, 孙希磊等 GB/T 46609-2025.
- **SuperEM, sub-meV超低阈值超导体耦合半导体探测器方案提出人** Talk by X.L. Sun at NDIP 2026, CHEP2026; Paper by A.Q. Gao, X.L. Sun et al. arXiv:2509.11954.

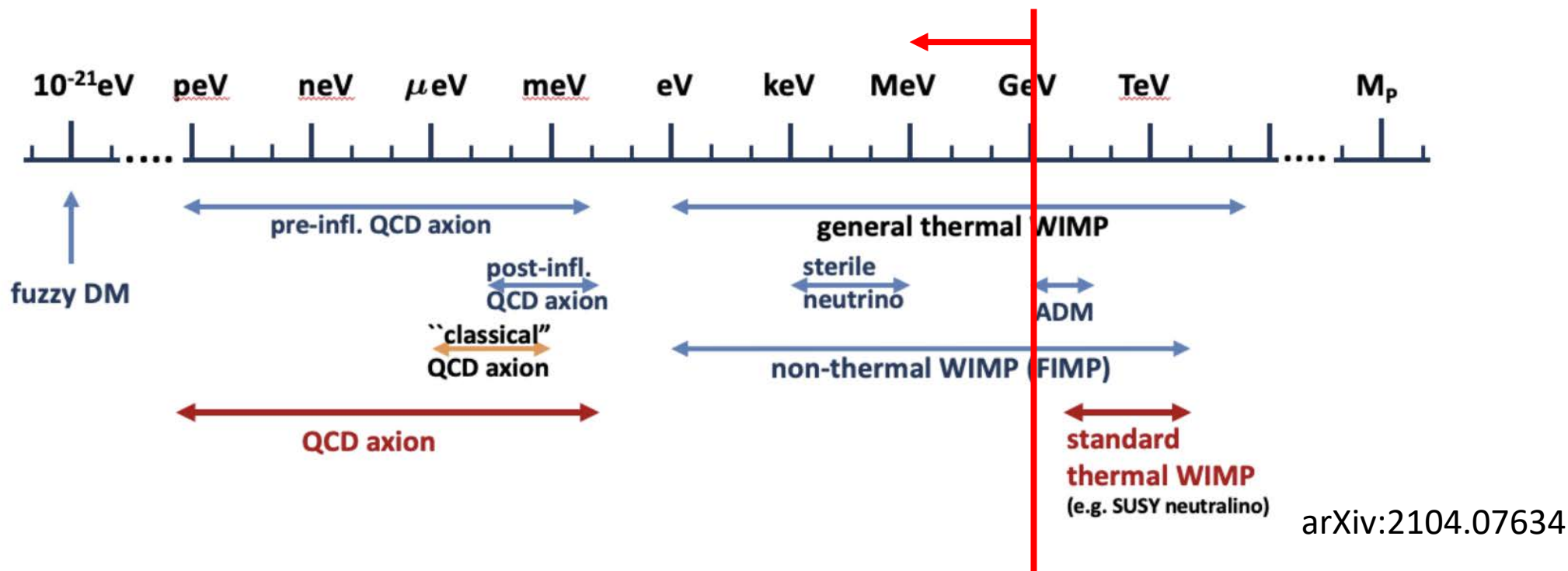


- **Motivation**
- **The SuperEM Proposal**
- **Principle Calculation and Simulation**
- **SiPM Characterization at 10 mK**
- **Physics Reach & Applications (DM, CvB, CEvNS)**
- **Summary & Outlook**

Dark Matter Searches

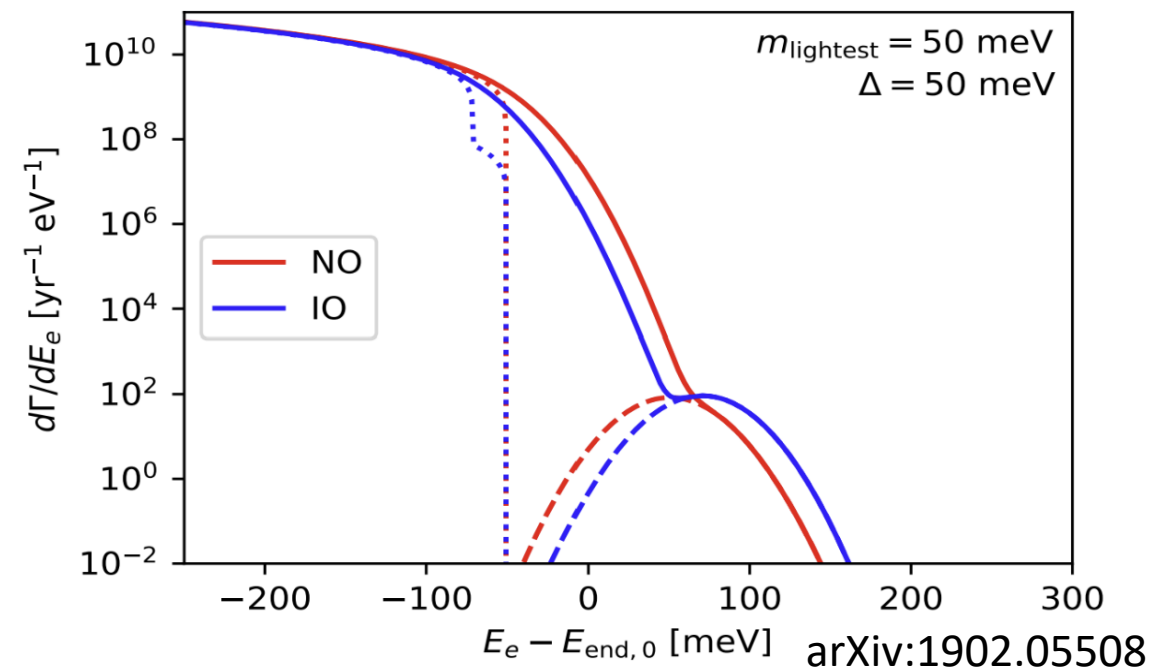
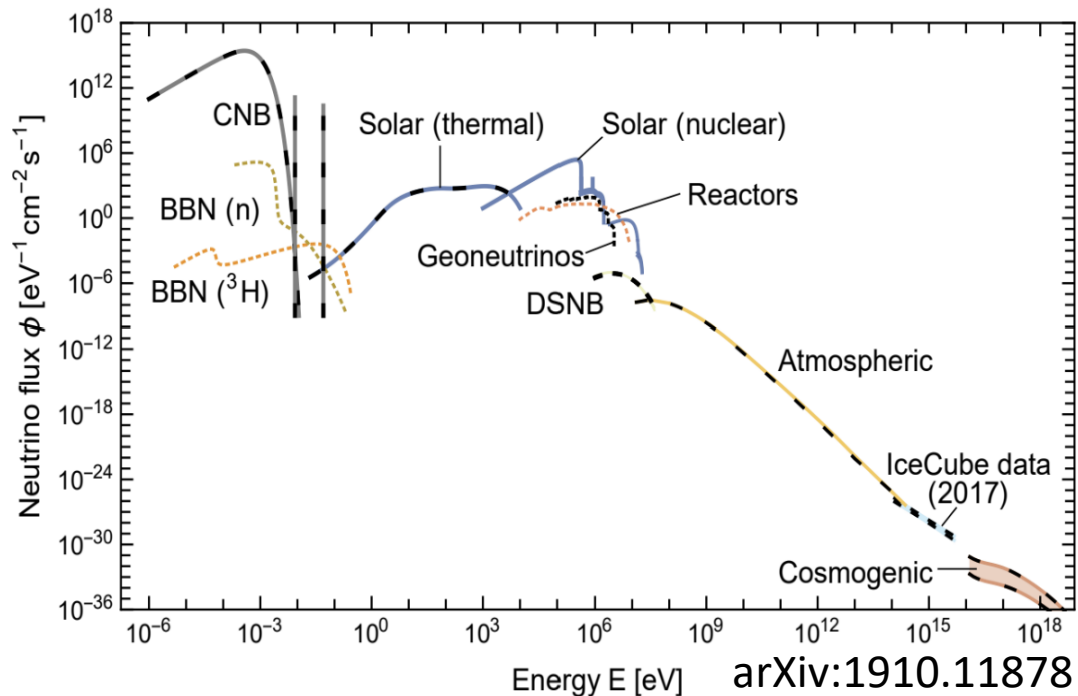


- **The Sub-GeV Frontier:** Exploring Light Dark Matter (LDM) requires strictly sub-meV energy thresholds.
- **The Scalability Challenge:** Future observatories demand massively multiplexed detector arrays with large target masses.



Cosmic Neutrino Background Searches

- **Absolute Energy Resolution:** ≤ 50 meV FWHM is required to resolve CvB and neutrino mass orderings.
- **The Pile-Up Issue:** Requires nanosecond-scale readout to survive the massive tritium beta-decay flux without signal overlap.



Cosmic Neutrino Background Searches

- **Parametric Fluorescence proposal:** 10 meV sensitivity is required to resolve CvB.

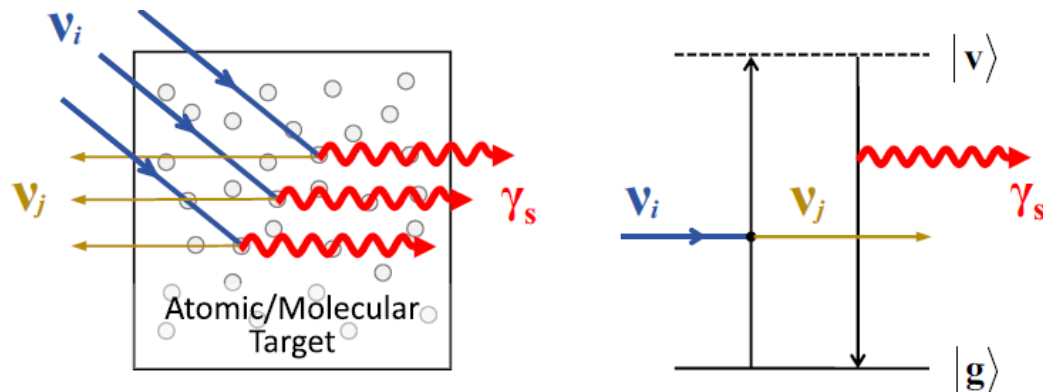
199. 通过参量荧光效应探测宇宙中微子背景

Guoyuan Huang (中国地质大学 (武...)

7/15/26, 2:48 PM

分会邀请报告 分会4: 中微子物理、粒...

宇宙大爆炸约1秒后, 中微子便从高温致密的等离子体...
度已冷却至约1.95 K。由于中微子只发生弱相互作用,
PTOLEMY实验。但其探测灵敏度受到量子不确定性关



Phys. Rev. Lett. **136**, 081003 (2026)

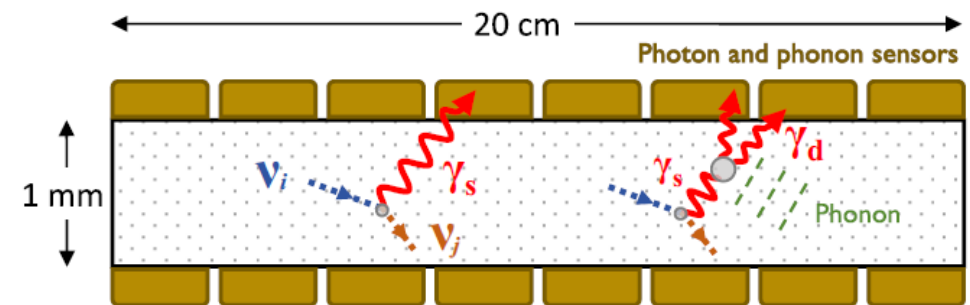
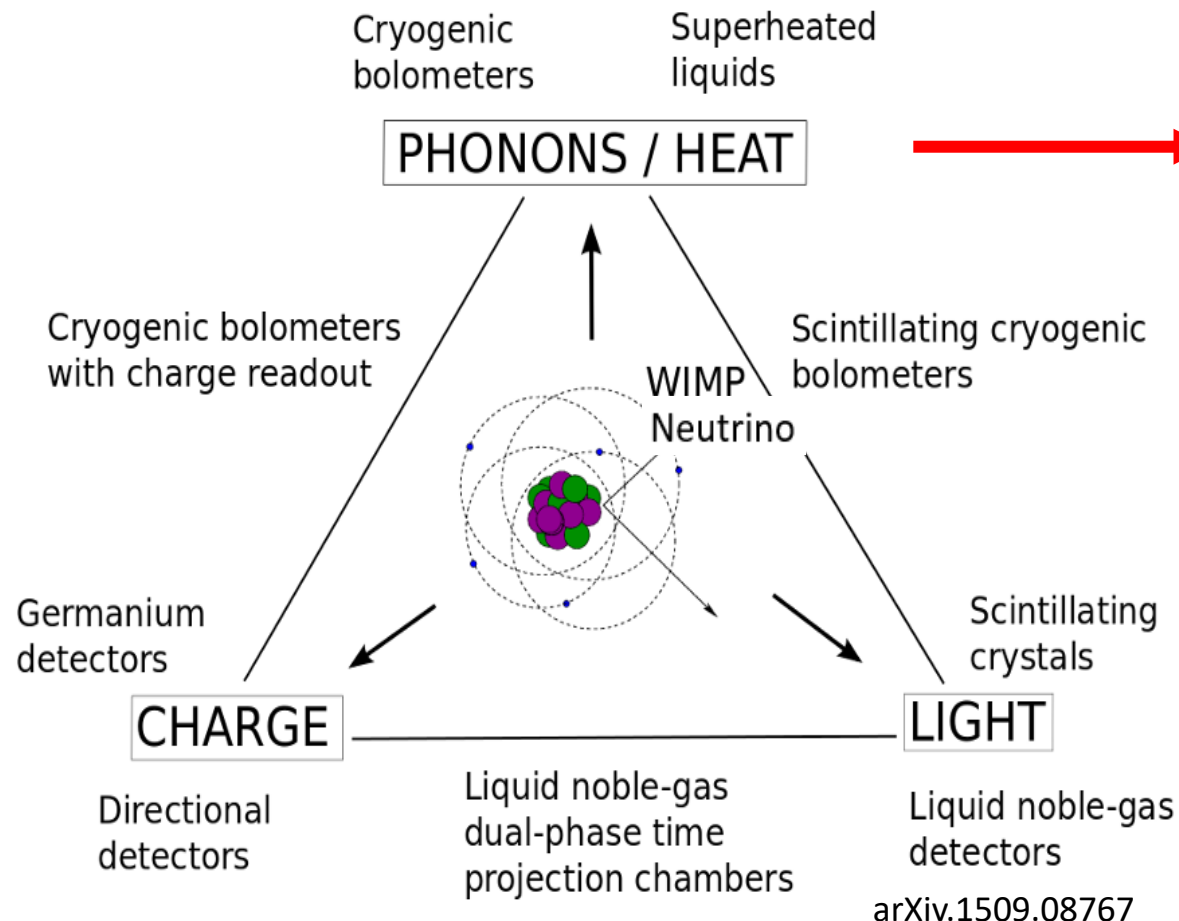


FIG. 3. A schematic plot of the experimental setup for detecting parameter fluorescence. The target is a solid film with dimensions $20\text{ cm} \times 20\text{ cm} \times 1\text{ mm}$. Its surface is covered with superconducting photon and phonon sensors featuring $\mathcal{O}(10\text{ meV})$ sensitivities. Two types of signals can arise, depending on whether the initial photon is absorbed by the medium before reaching the sensors. Similar geometry may be found in experiments searching for light dark matters [71,72].

How to reach meV threshold?

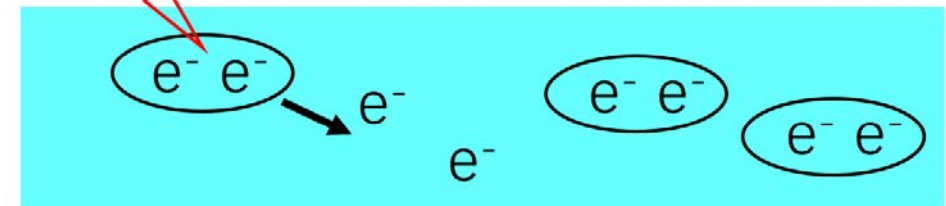
- Atomic energy gap, eV level threshold, Charge and Light
- Cooper pair energy gap, sub-meV, Phonon



- Superconducting Tunnel Junctions (STJs)
- Kinetic Inductance Detectors (KIDs / MKIDs)
- Transition Edge Sensors (TES)
- Nanowire Single-Photon Detectors (SNSPDs)
- Qubit-Based Sensors (QPD/QCD)

Sub-meV, ns, and scalability are the impossible triangle, can not achieve simultaneously

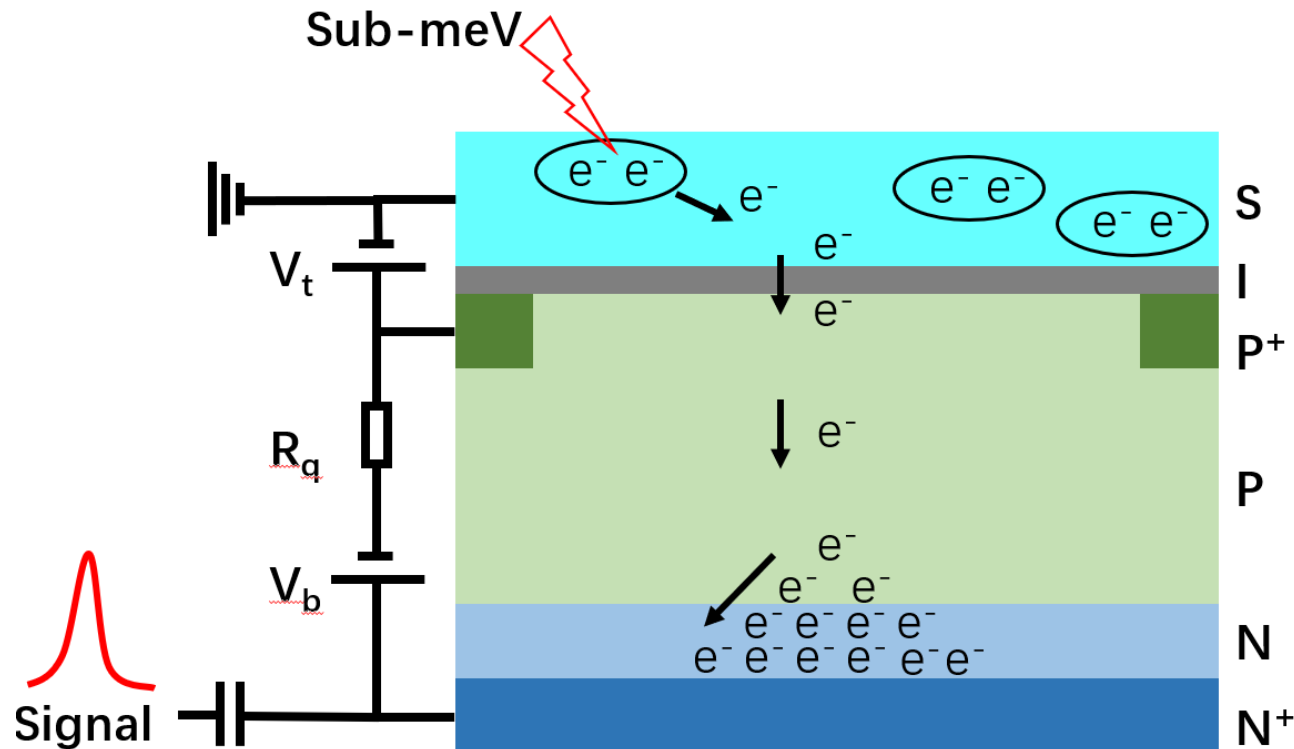
Sub-meV



SuperEM Proposal



■ Superconductor-Coupled Semiconductor Electron-Multiplying Detector



Architectural Framework (S-I-P-N):

- Superconducting Absorber (S-Layer)
- Quantum Tunneling Barrier (I-Layer)
- Charge Multiplication Region (P-N Junction)

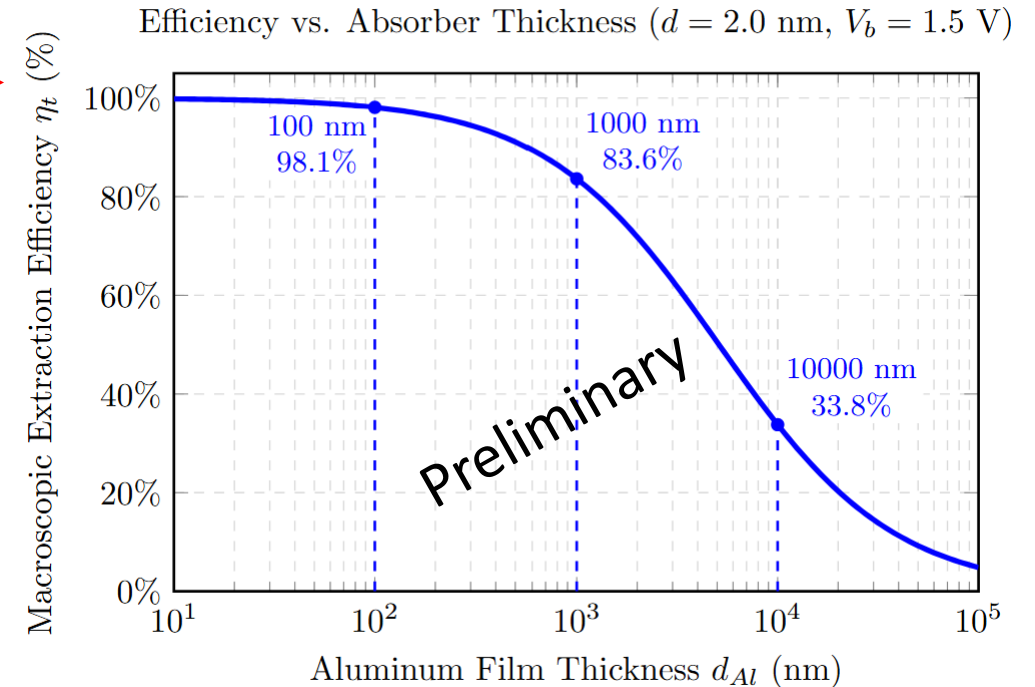
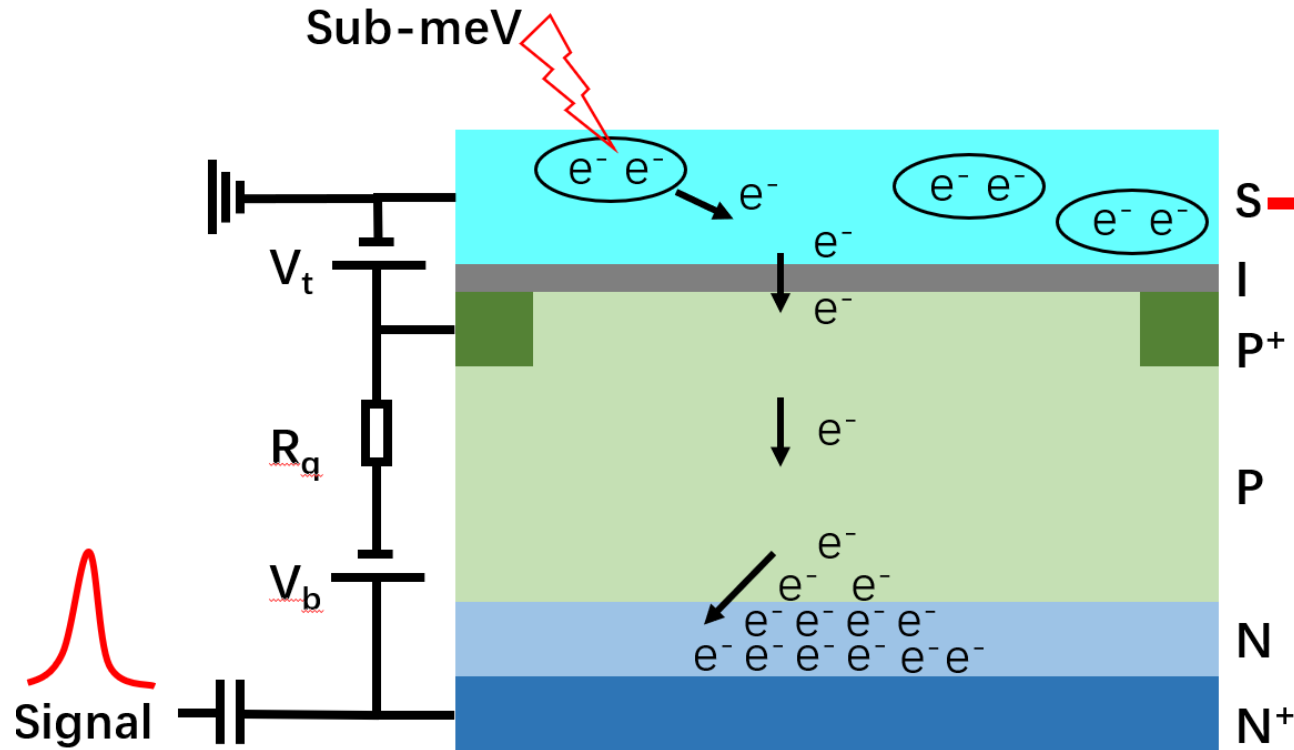
Key Features:

- Sub-meV threshold and high gain
- Nanosecond level Response, non-thermal equilibrium
- Good Scalability, Compatible with semiconductor processes
- Tunable Quantum Gating via I-Layer bias V

SuperEM Extraction Efficiency

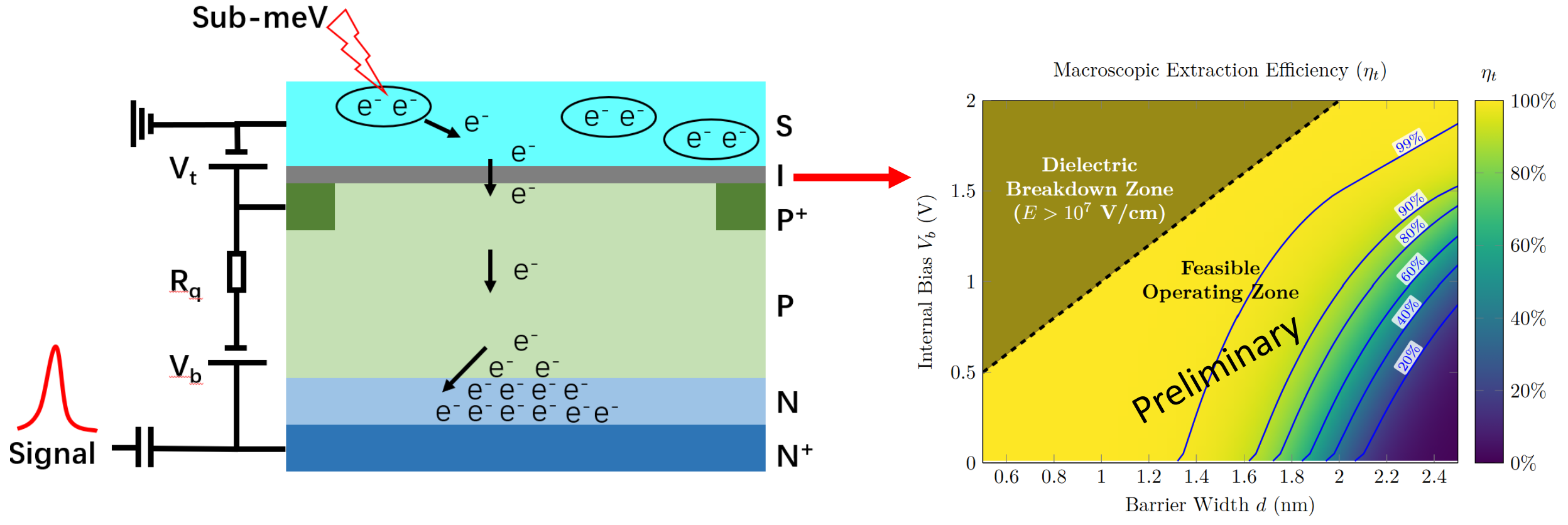


- Thinning the superconducting aluminum absorber to 100 nm yields an excellent macroscopic extraction efficiency of 98.1%



SuperEM Extraction Efficiency

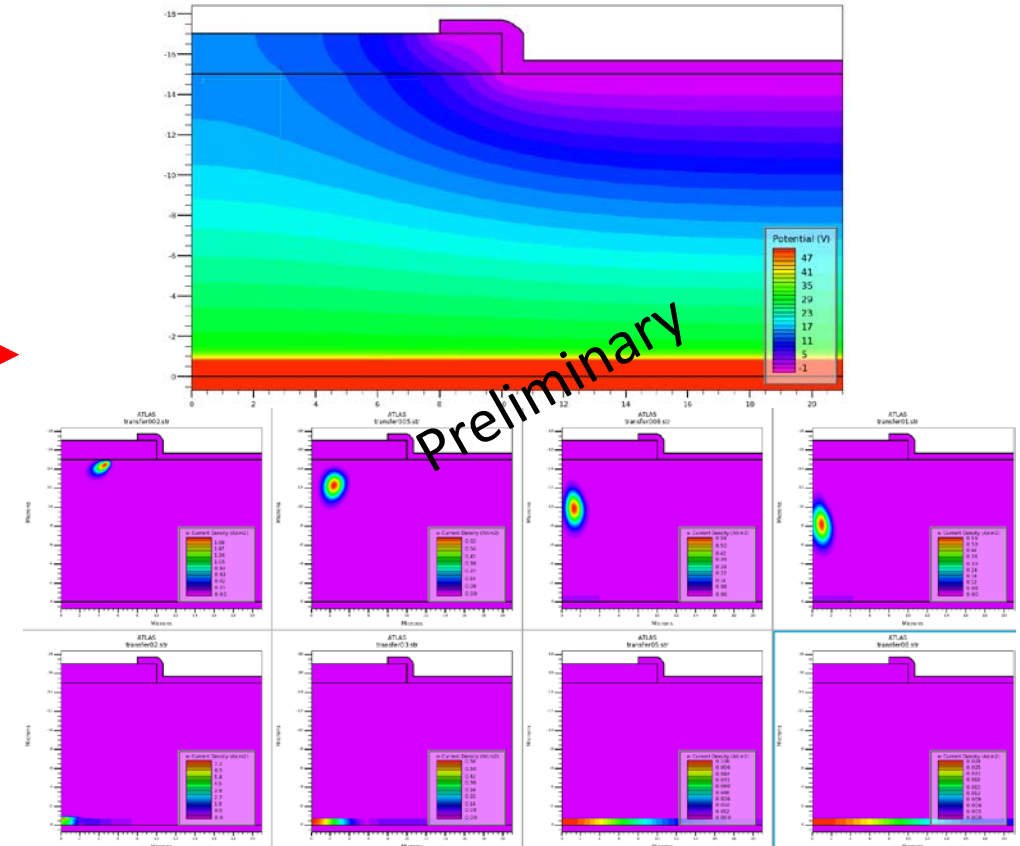
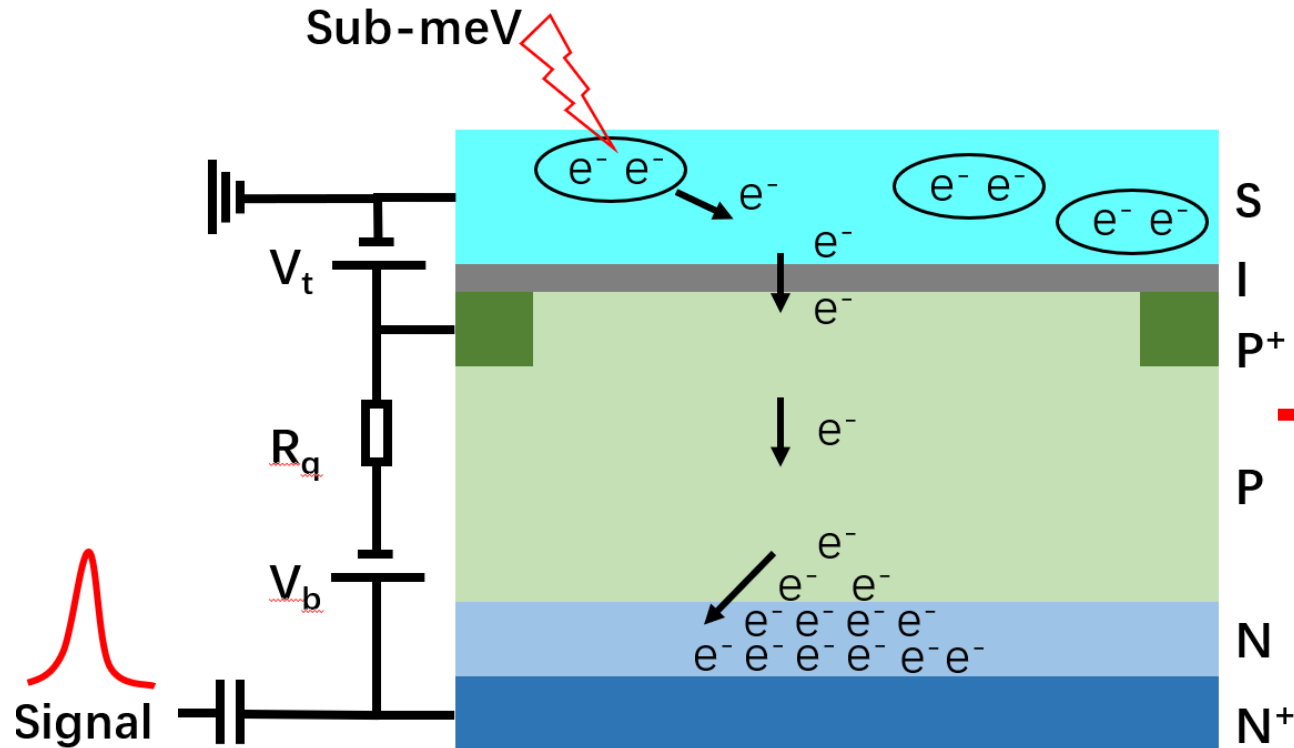
- Furthermore, tuning the internal bias and barrier width reveals a broad, feasible operating zone that avoids dielectric breakdown while maintaining efficiency



TCAD Signal Transport & Drift Simulation

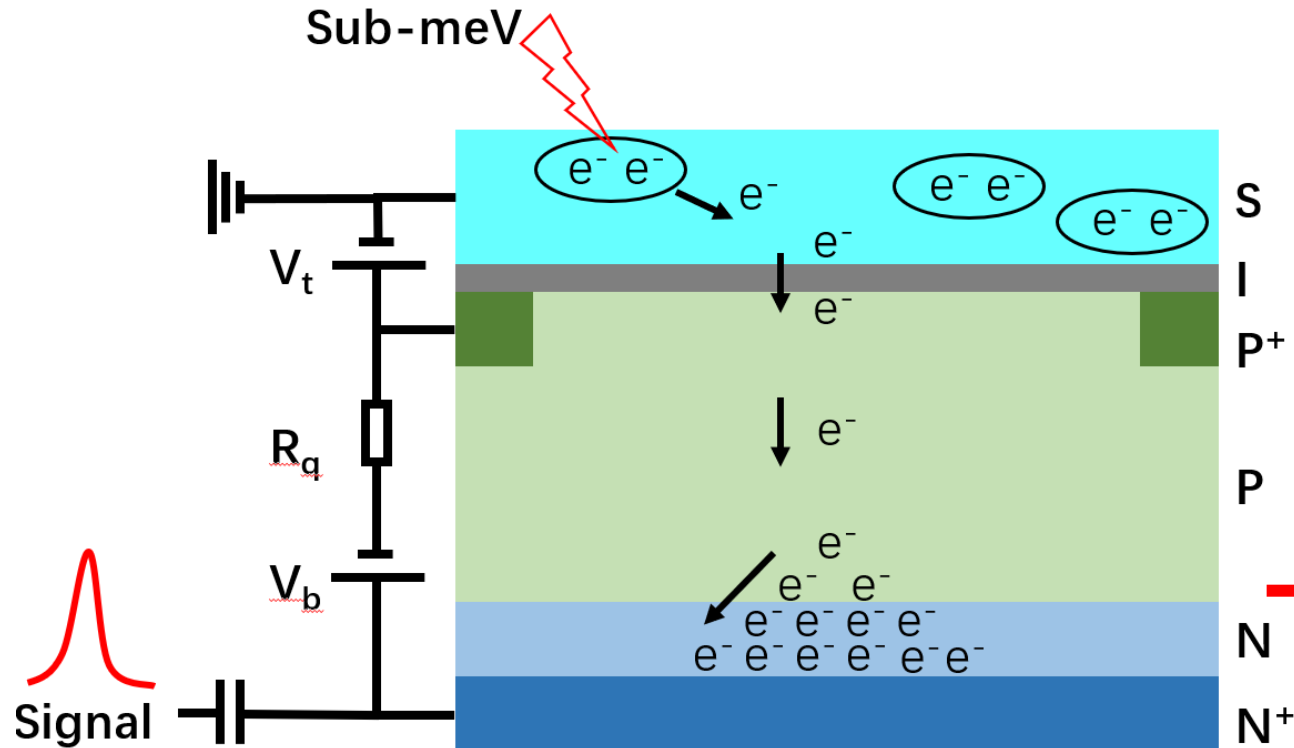


- **Undoped Interface & High Field:** Immediately forces electrons into vertical drift preventing lateral diffusion, $\geq 95\%$ Drift Survival.



Electron-Multiplying or Carrier Freeze-out

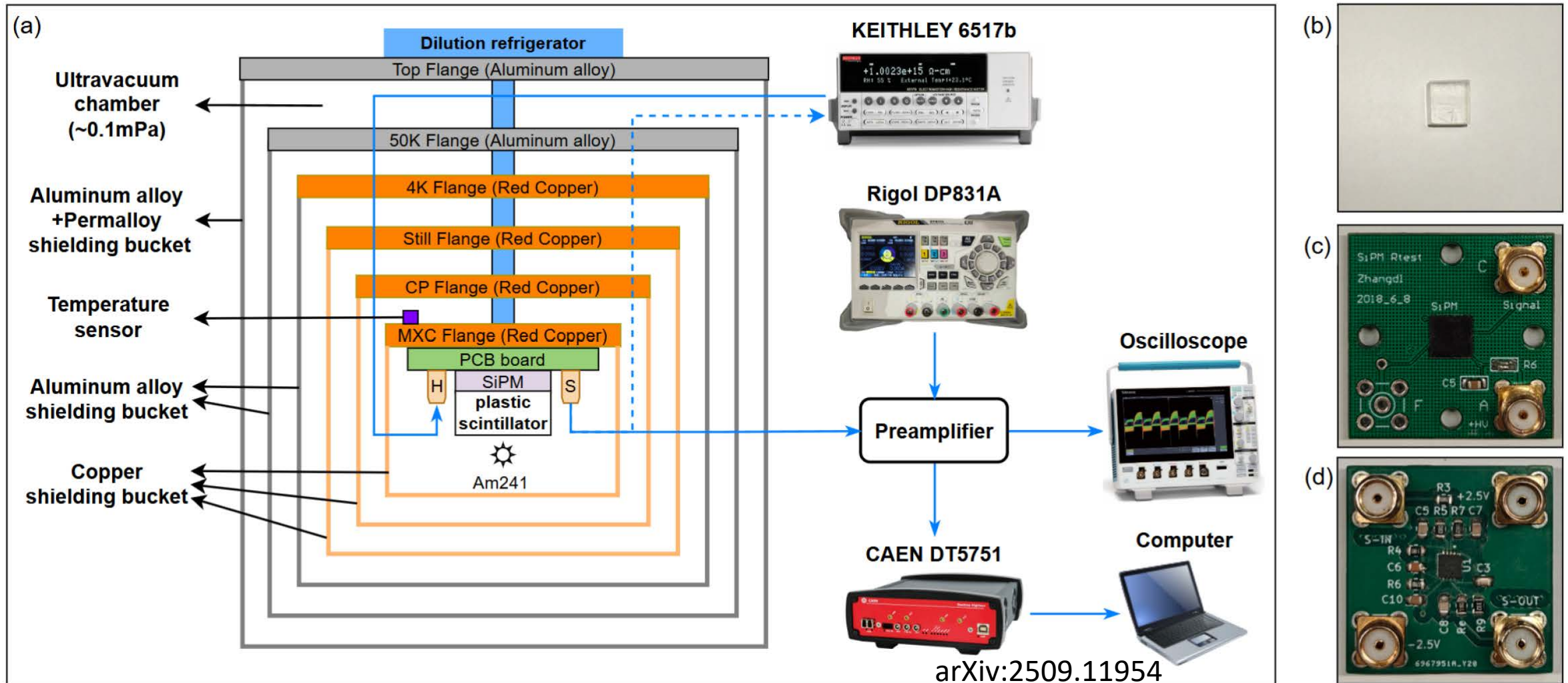
- One of the big questions to answer is whether electrons can drift and multiply within a semiconductor at a temperature of 10 mK



Whether a p-n junction can achieve electron multiplication at a temperature of 10 mK???
Carrier Freeze-out Effect

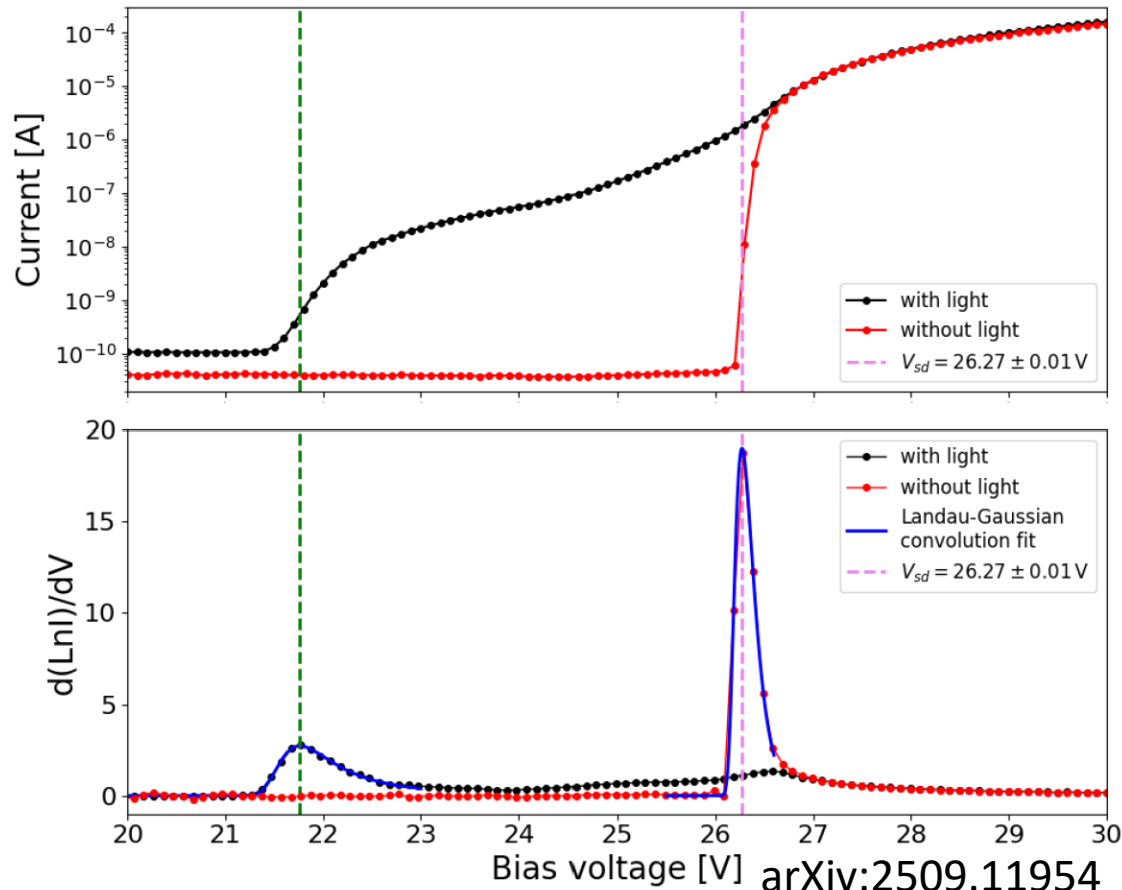
Characterization of SiPM at 10 mK

- A dilution refrigerator test platform, $\text{PS} + {}^{241}\text{Am}$ as light source, SensL J 6 mm SiPM

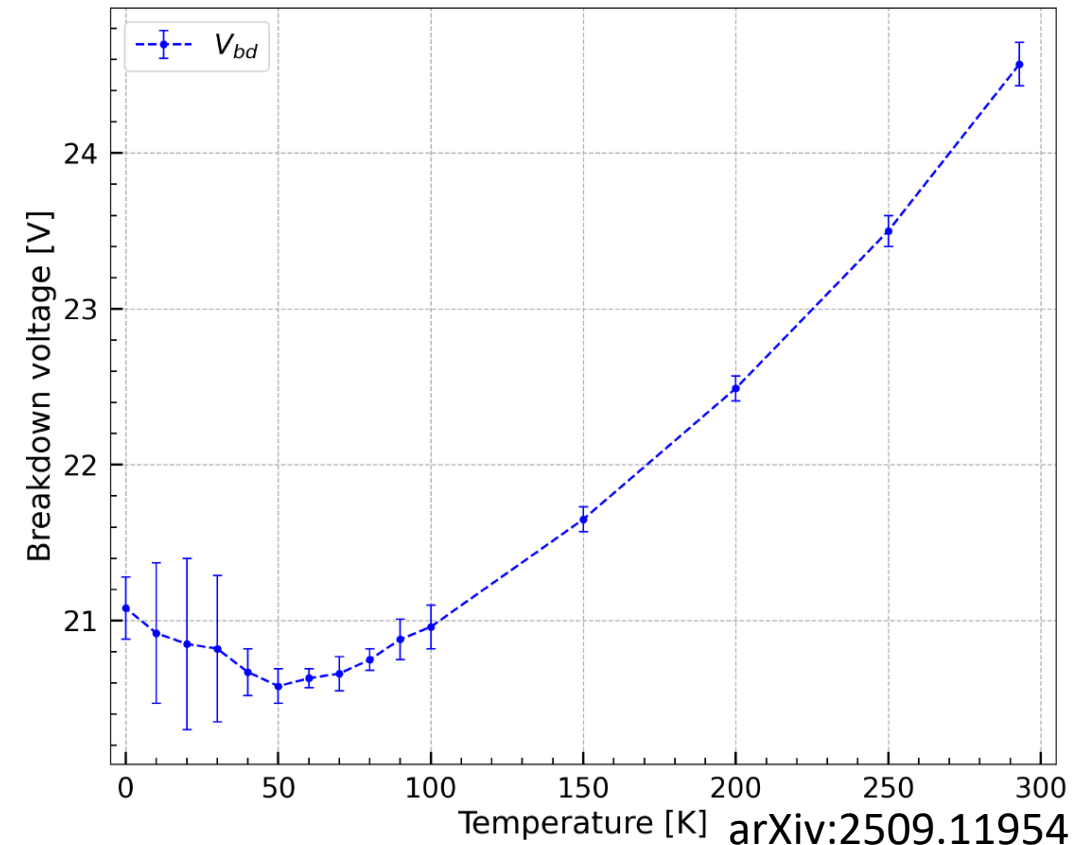


I-V curve and Breakdown Voltage at 10 mK

- The breakdown voltage displays a non-linear temperature dependence, there is an inflection point at 50 K, followed by a slow rise.



IV curves and their differential curves of the SiPM at 10 mK

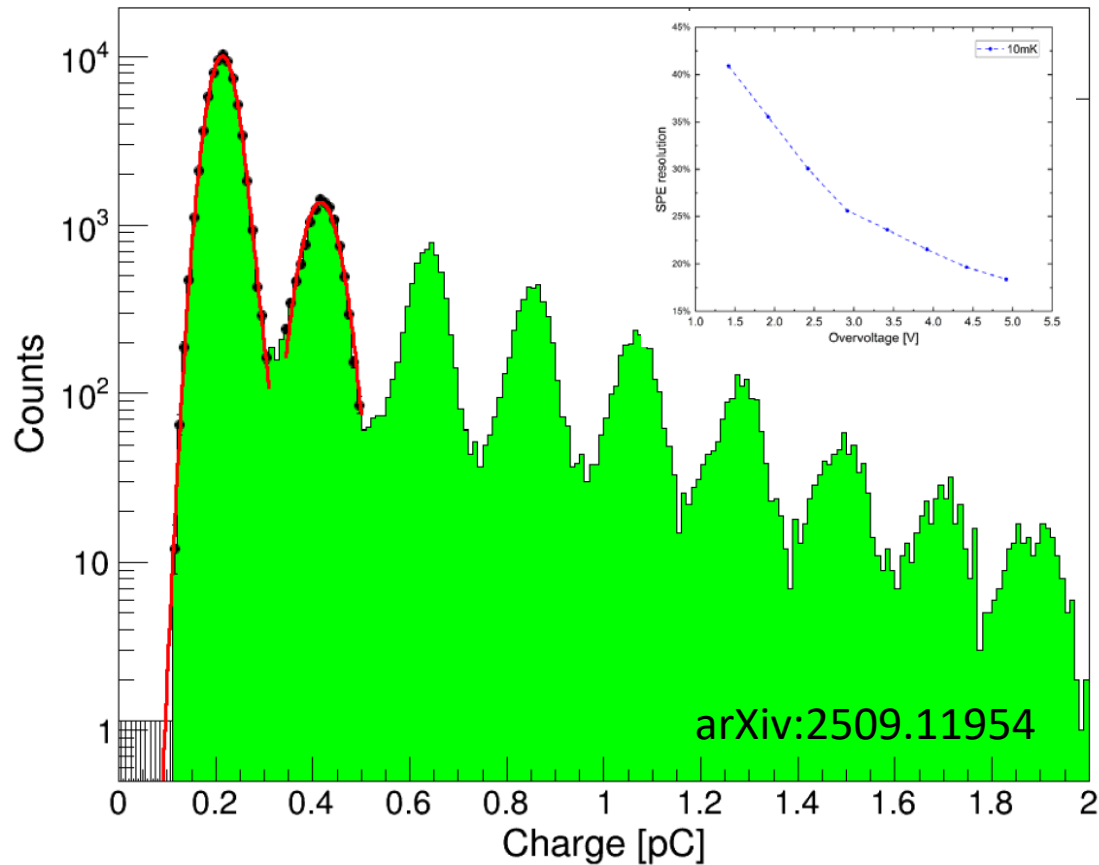


Temperature dependence of V_{bd} over the temperature range from 300 K to 10 mK.

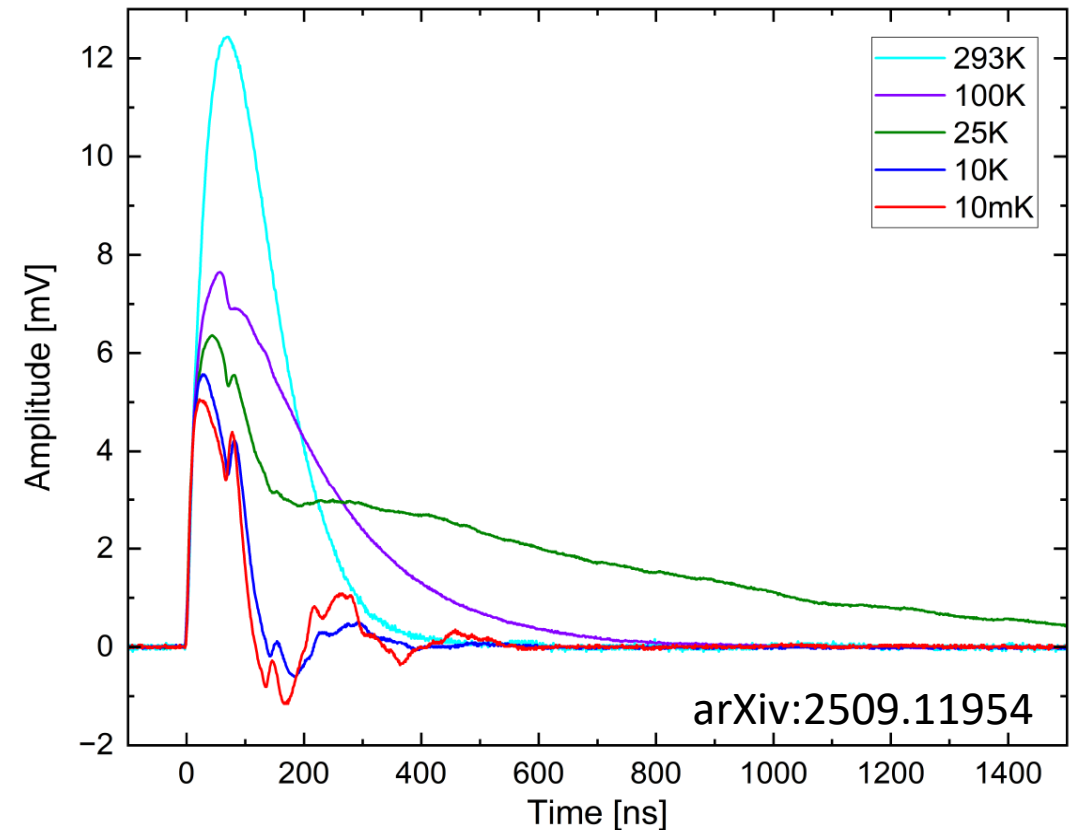
Single p.e. Waveform and Resolution at 10 mK



- At 10 mK, the SiPM maintains good single photoelectron (SPE) resolution.
- Pulse width undergoes a significant change: as the temperature decreases, it first widens and then narrows.



Single p.e. resolution 10 mK

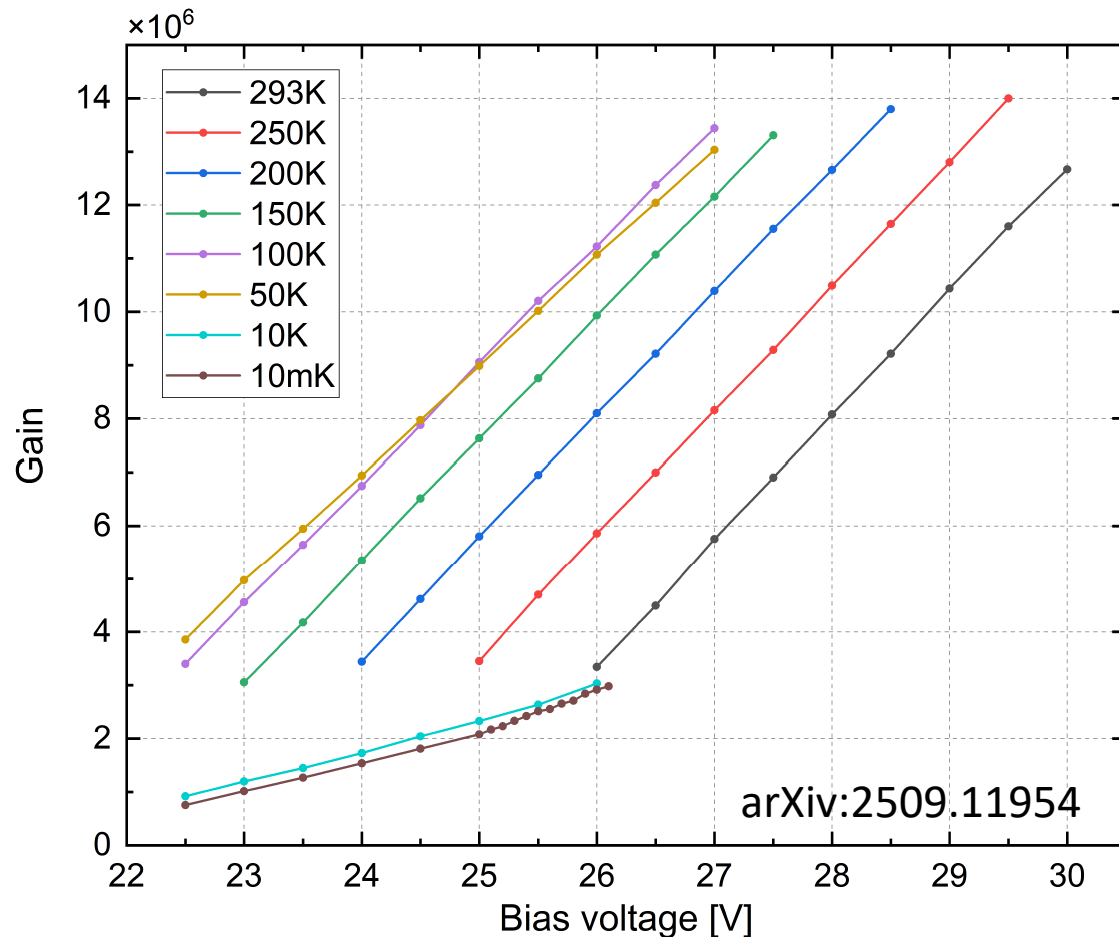


SiPM single p.e. waveform signals at different temperatures

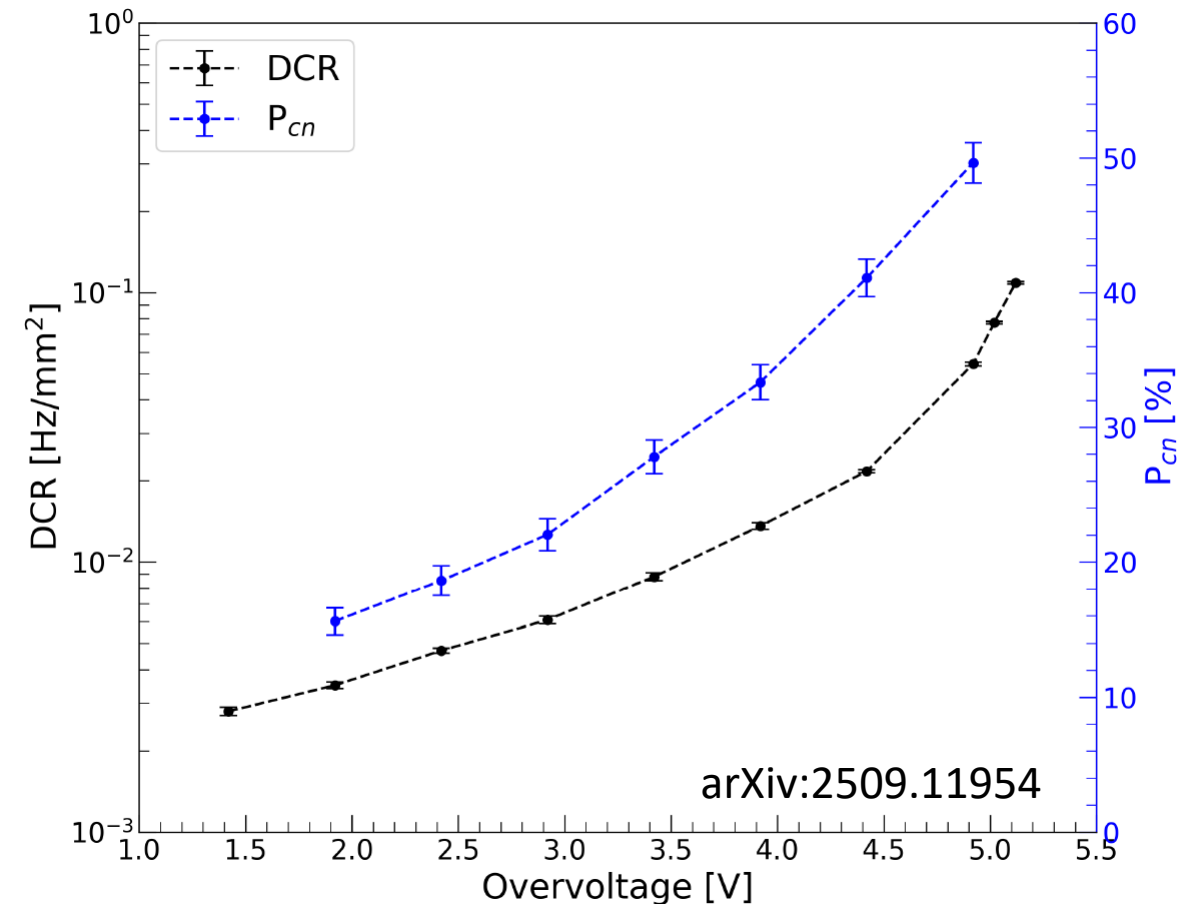
Gain and DCR at 10 mK



- Linear relationship between gain and bias voltage remains from room temperature down to 10 mK, DCR down to 10^{-3} Hz/mm² at 10 mK, important for rare event search



SiPM gain versus bias voltage from 293 K to 10 mK

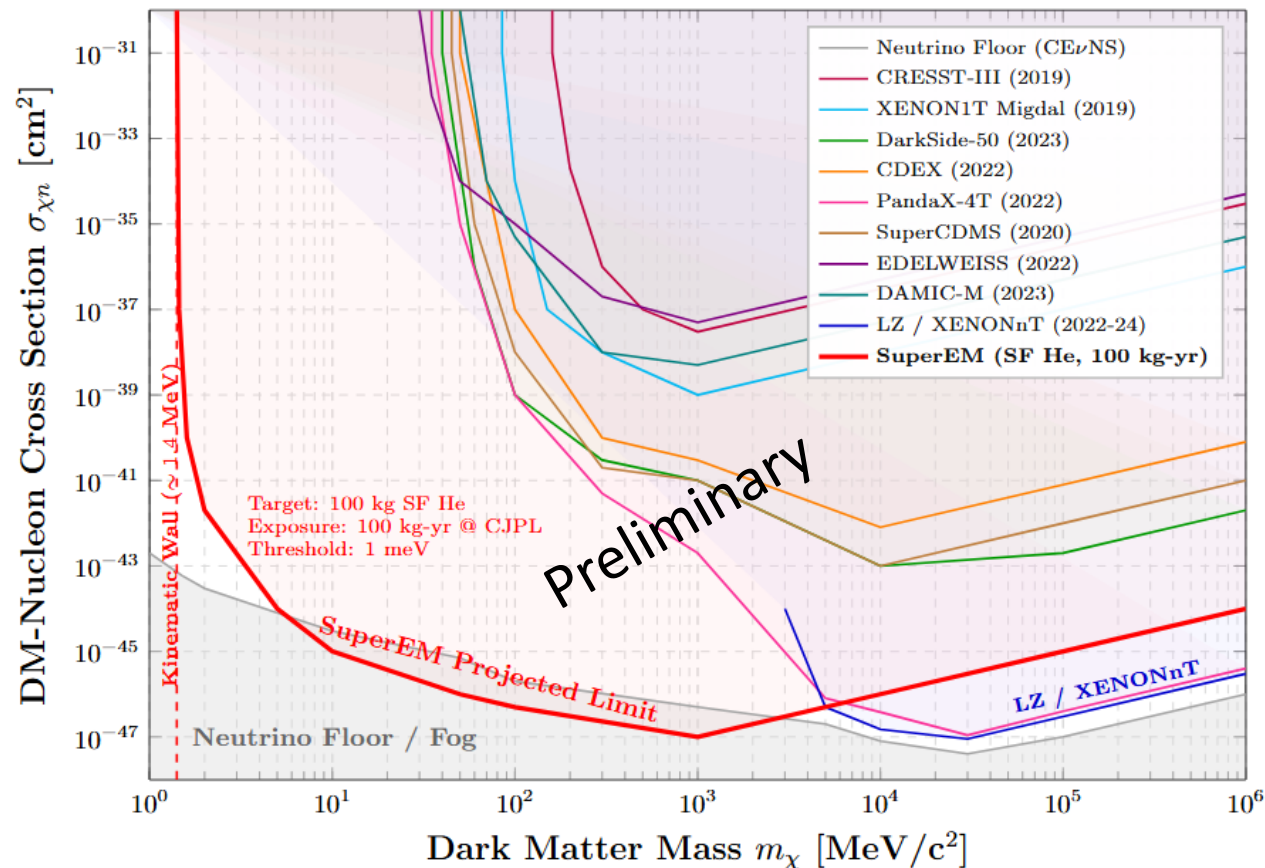


DCR and CT as a function of overvoltage at 10 mK

Projected LDM & WIMP Sensitivity

- Target: 100 kg Superfluid Helium.
- 1 meV threshold will push DM sensitivity down to the 1 MeV limit.

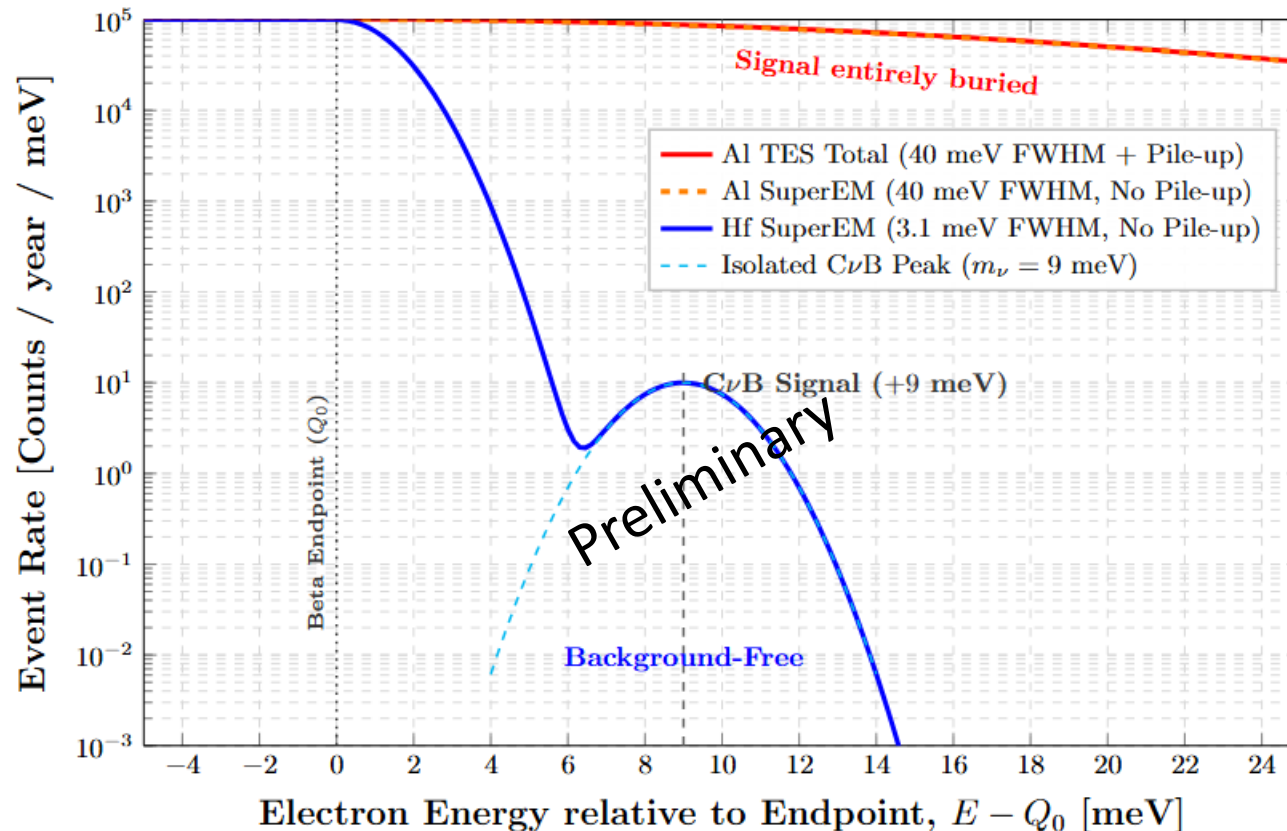
Projected LDM & WIMP Sensitivity: SuperEM with 100 kg SF He



PTOLEMY 9 meV Discovery (Normal Ordering)

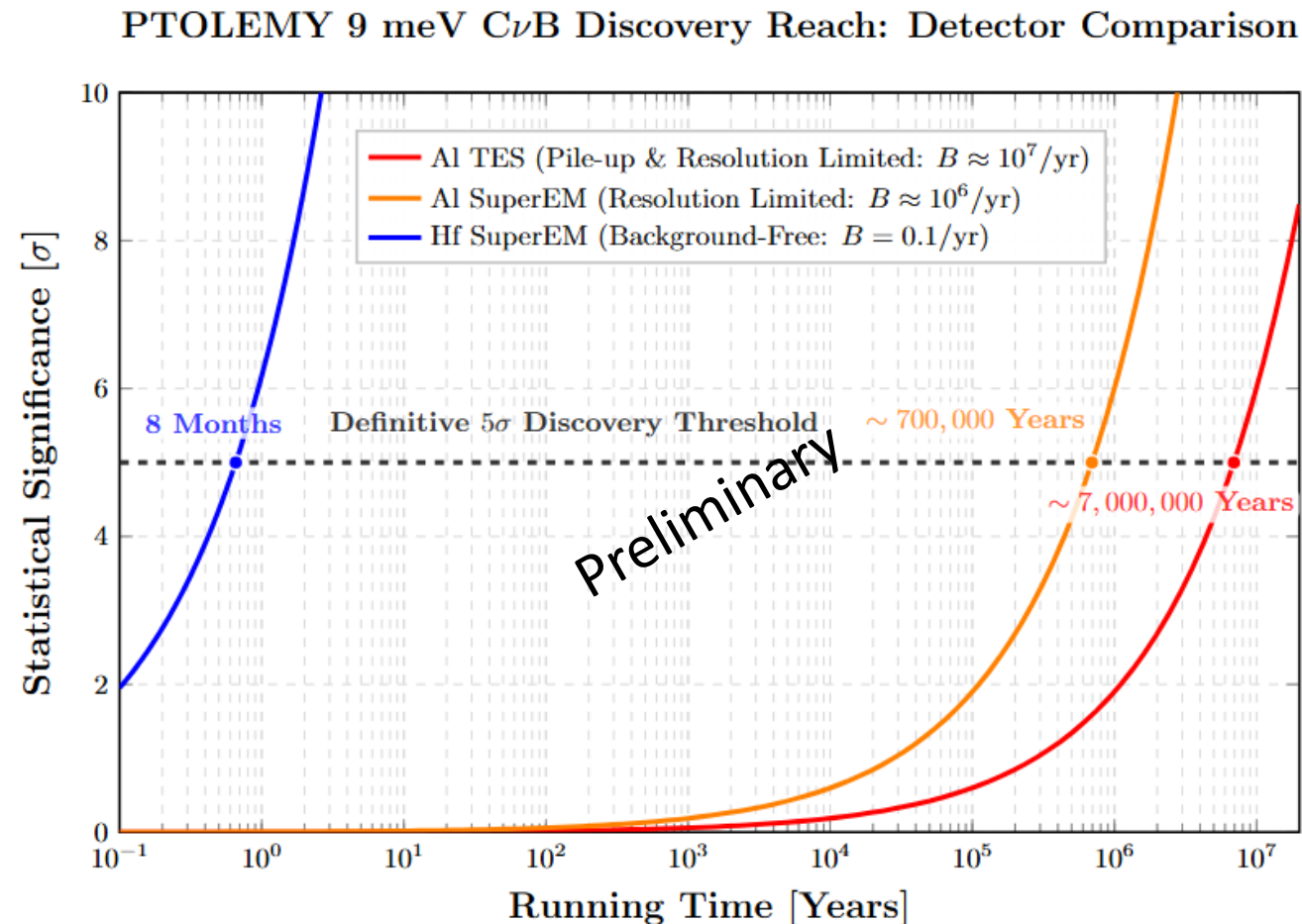
- **Hafnium (Hf) SuperEM:** Ultra-low gap (0.02 meV) yields a sharp 3.1 meV FWHM resolution at 100 meV.
- **Zero Pile-up:** Nanosecond response isolate the CvB signal from the beta-decay endpoint.

PTOLEMY 9 meV $\text{C}\nu\text{B}$ Discovery: Hf SuperEM vs. Al Detectors



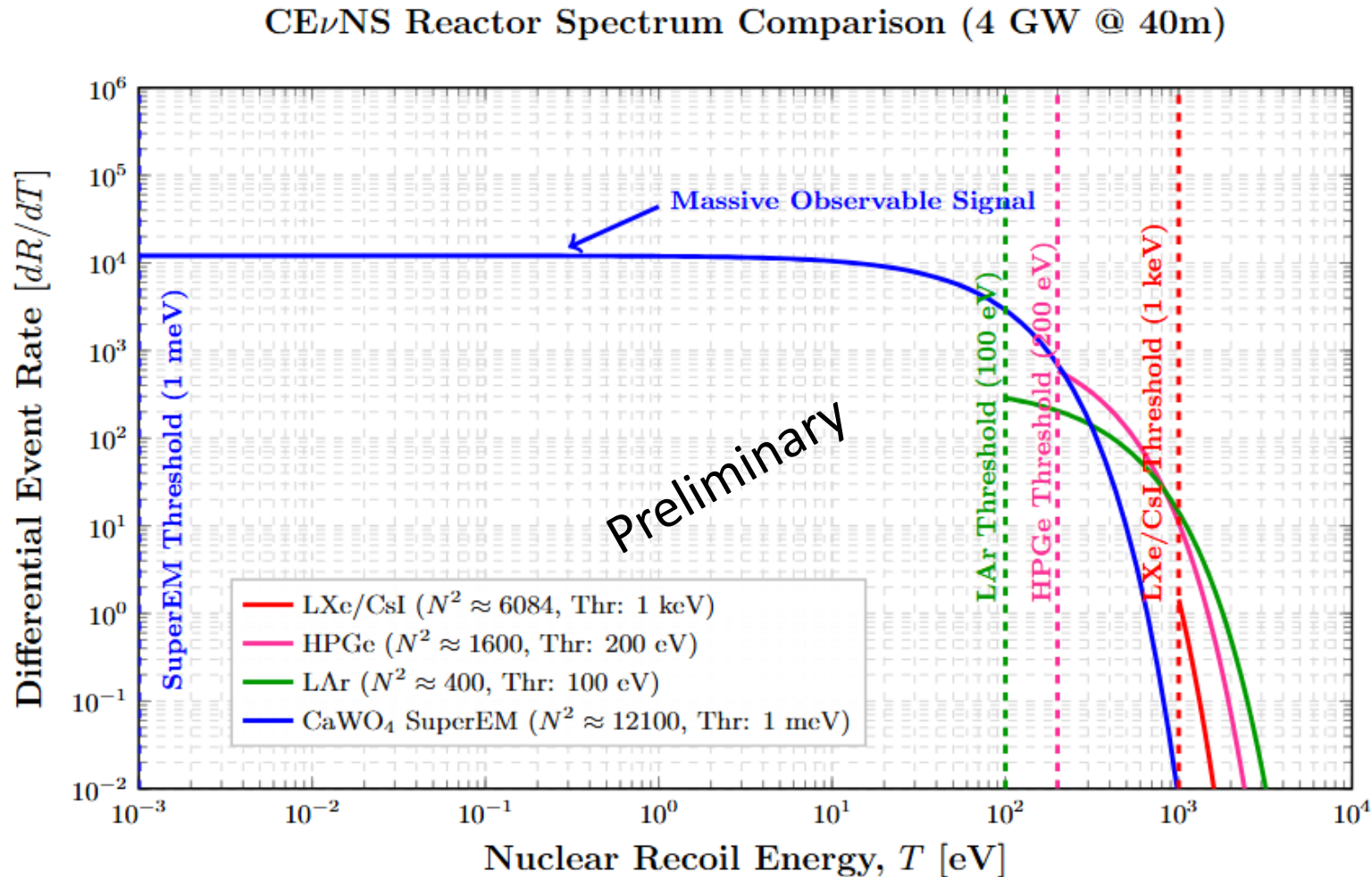
PTOLEMY CvB Discovery Sensitivity

- Background-free performance accelerates the CvB discovery timeline.
- 5 sigma Discovery: Achieved in just 8 months.



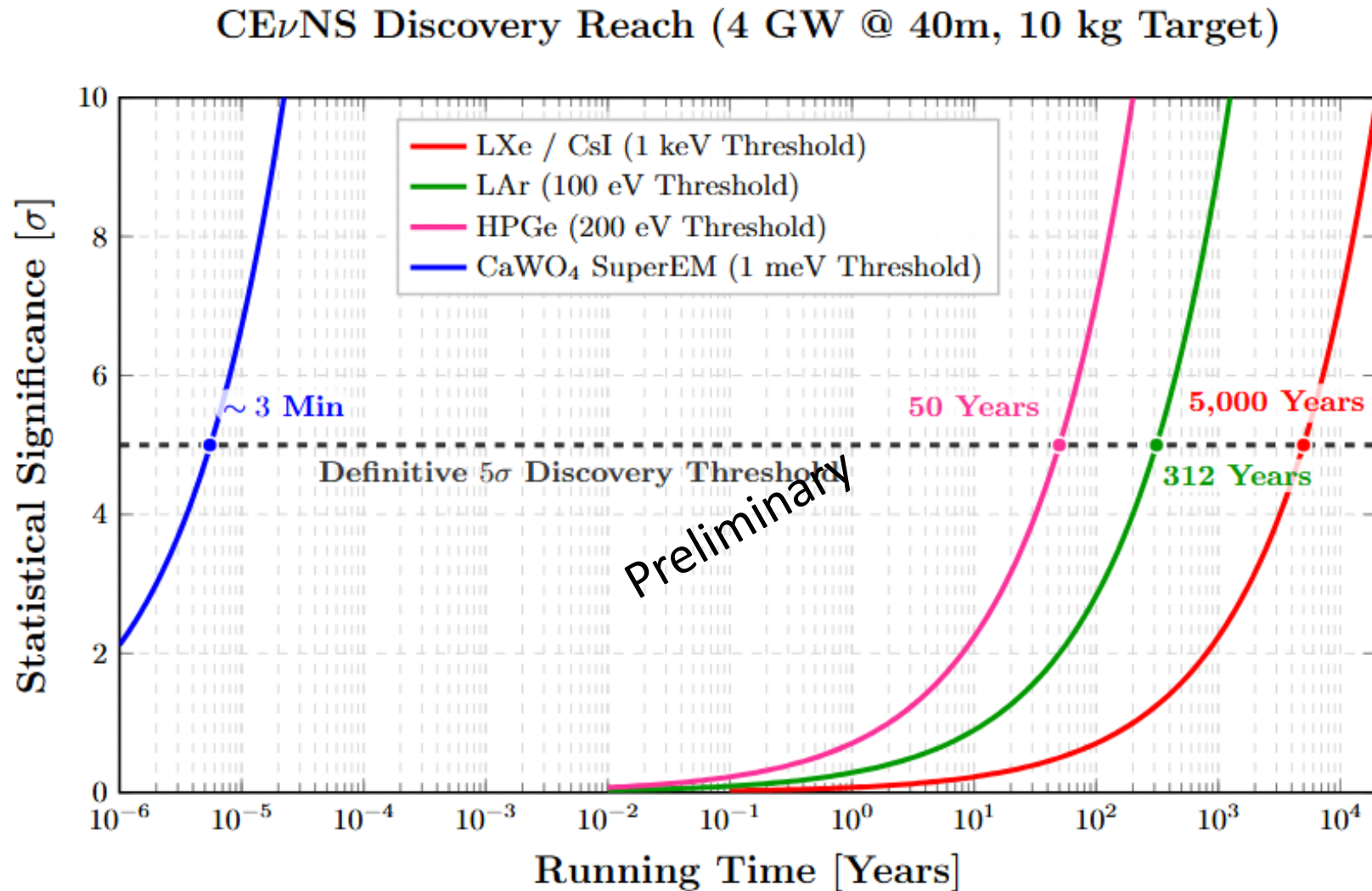
Reactor CEvNS detection

- Unlocks access to observable signals orders of magnitude larger than current detectors.



Reactor CEvNS Sensitivity

- Enables a 10 kg•min scale CEvNS detector.





- **The SuperEM Architecture:** A novel S-I-P-N detector featuring sub-meV thresholds, nanosecond response times, and massive scalability.
- **Empirical Milestone:** SiPM avalanche amplification has been successfully verified at 10 mK.
- **Current Status:** A fully integrated SuperEM prototype is currently in design/fabrication.
- **Physics Impact:** Redefine the limits of Dark Matter, CvB, CEvNS experiments.

Thank you for your attention!

